

SL32-ASF-Q1 THRU SL34-ASF-Q1

List

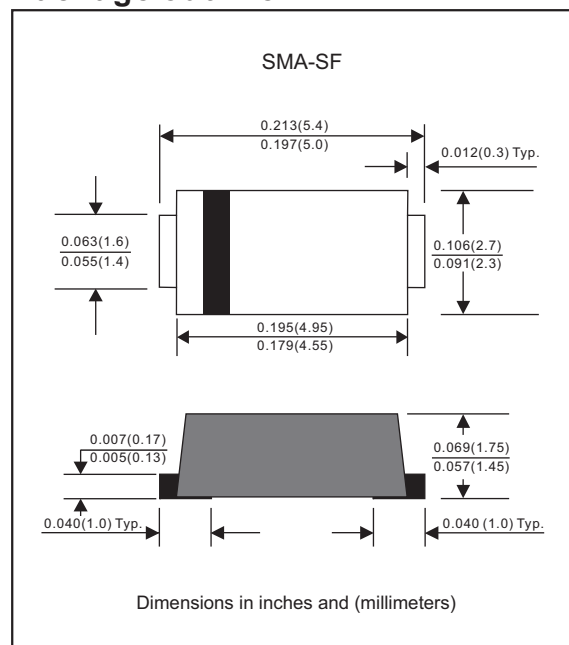
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SL32-ASF-Q1 THRU SL34-ASF-Q1**3.0A Low VF Surface Mount Schottky Barrier Rectifiers 20V-40V****Features**

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance
- Low profile surface mounted application in order to optimize board space
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- Guardring for overvoltage protection
- Ultra high-speed switching
- Silicon epitaxial planar chip, metal silicon junction
- Lead-free parts meet RoHS requirements
- Qualified to AEC-Q101 standards for high reliability
- Suffix "-H" indicates Halogen-free part, ex.SL32-ASF-Q1-H

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SMA-SF
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.04 gram

Package outline**Maximum ratings** (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOLS	SL32-ASF-Q1	SL33-ASF-Q1	SL34-ASF-Q1	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	Volts
Maximum RMS voltage	V_{RMS}	14	21	28	Volts
Maximum continuous reverse voltage	V_R	20	30	40	Volts
Maximum average forward rectified current	I_O	3.0			A
Non-repetitive peak forward surge current 8.3ms single half sine-wave	I_{FSM}	80			A
Typical diode junction capacitance (Note 1)	C_J	300			pF
Operating junction temperature range	T_J	-55 to +100			$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-65 to +175			$^{\circ}\text{C}$

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOLS	SL32-ASF-Q1	SL33-ASF-Q1	SL34-ASF-Q1	UNITS
Maximum instantaneous forward voltage at $I_F=3.0A$	V_F	0.38	0.40	0.40	Volts
Maximum reverse leakage current at rated V_R $T_J=25^{\circ}\text{C}$ $T_J=75^{\circ}\text{C}$	I_R	1.0 20			 mA mA

Thermal characteristics

PARAMETER	SYMBOLS	SL32-ASF-Q1	SL33-ASF-Q1	SL34-ASF-Q1	UNITS
Typical thermal resistance junction to ambient (Note 2)	$R_{\theta JA}$	43			$^{\circ}\text{C/W}$
Typical thermal resistance junction to case (Note 2)	$R_{\theta JC}$	26			$^{\circ}\text{C/W}$

Notes 1: Measured at 1 MHz and applied reverse voltage of 4.0 VDC
 2: Mounted on FR-4 PCB copper, minimum recommended pad layout

Rating and characteristic curves (SL32-ASF-Q1 THRU SL34-ASF-Q1)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

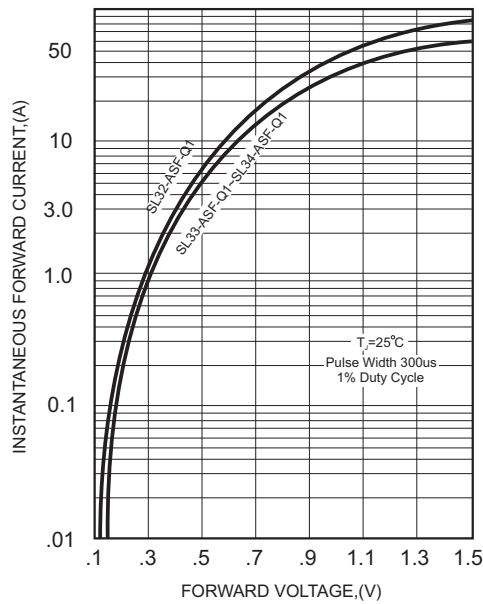


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

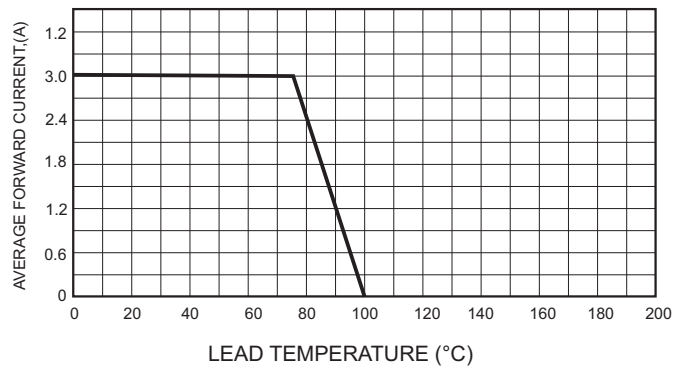


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

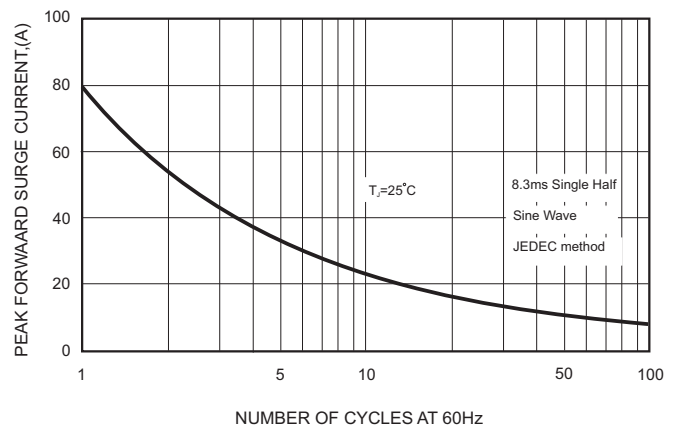


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

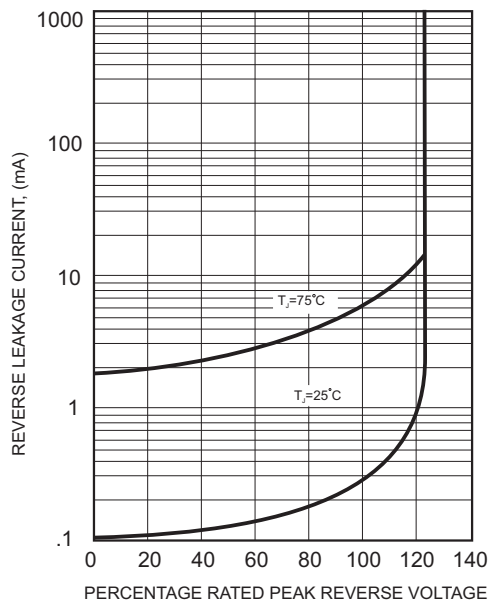
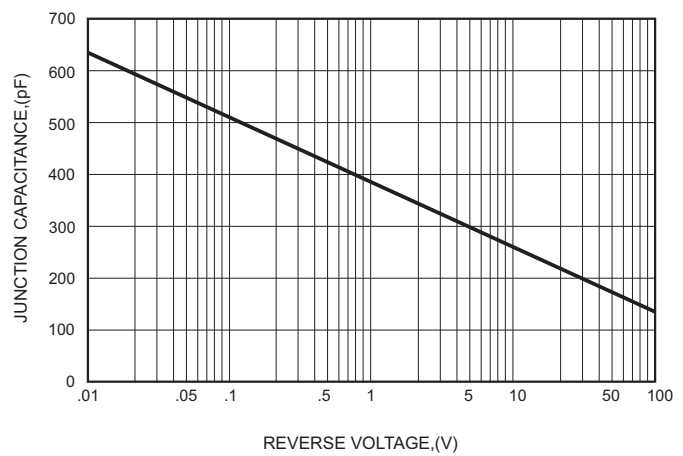


FIG.5-TYPICAL JUNCTION CAPACITANCE



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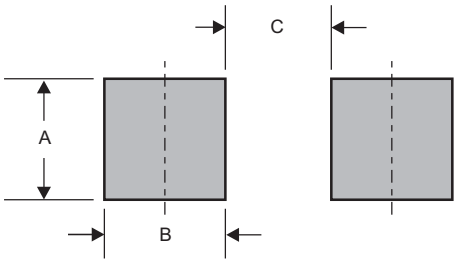
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
SL32-ASF-Q1	SL32
SL33-ASF-Q1	SL33
SL34-ASF-Q1	SL34

Suggested solder pad layout

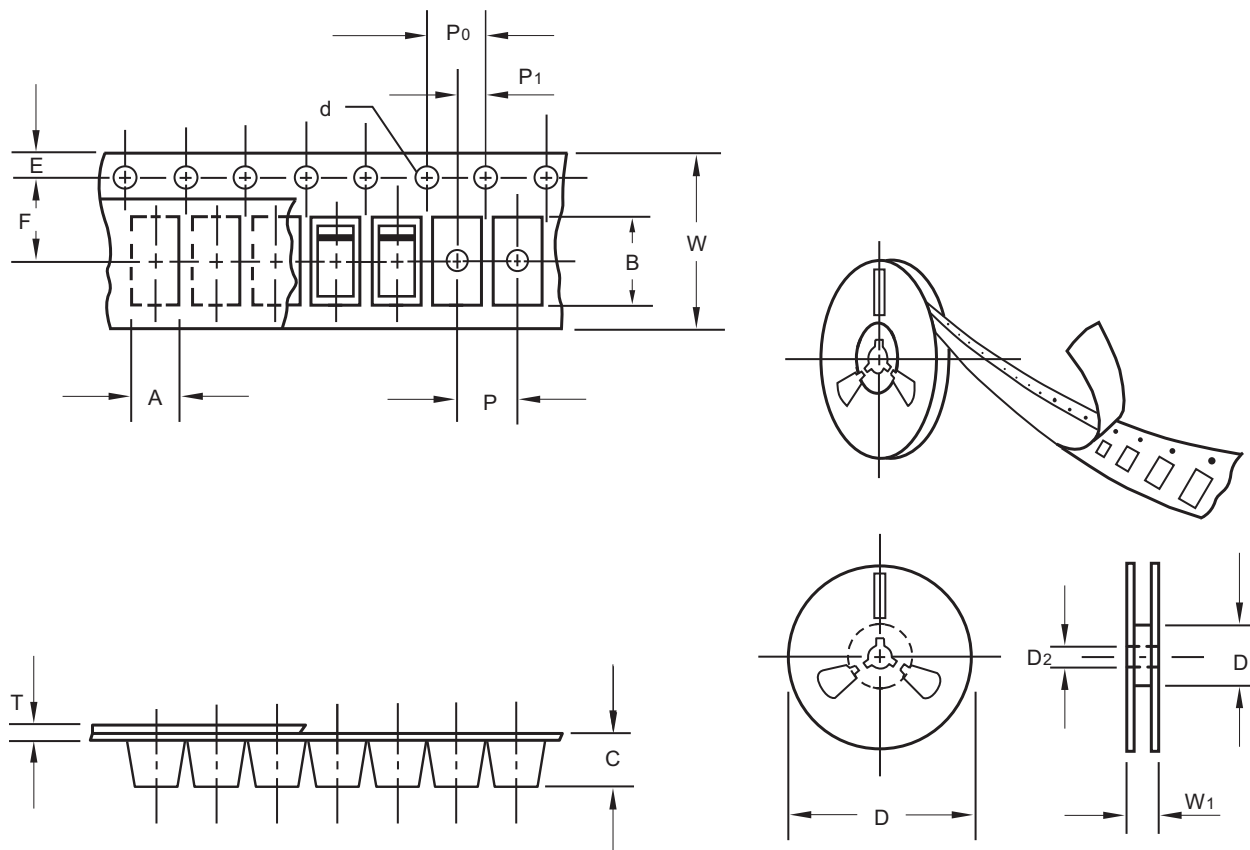


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SMA-SF	0.063 (1.60)	0.059 (1.50)	0.110 (2.80)

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Packing information



unit:mm

Item	Symbol	Tolerance	SMA-SF
Carrier width	A	0.1	2.90
Carrier length	B	0.1	5.50
Carrier depth	C	0.1	2.10
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D1	min	50.00
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

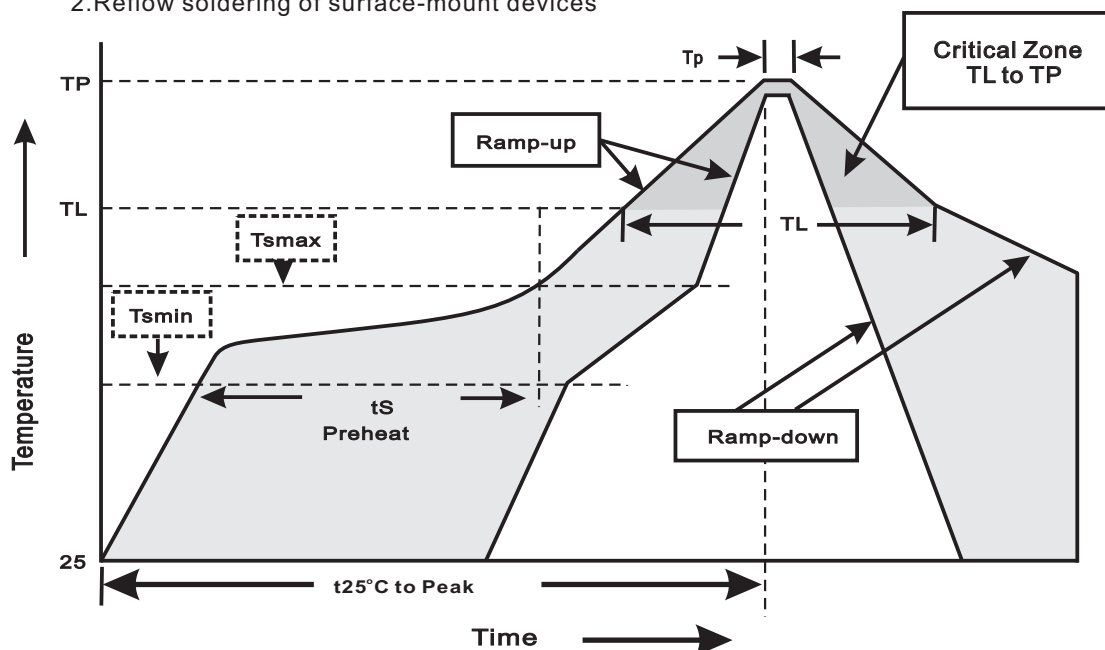
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SMA-SF	7"	2,000	4.0	20,000	183*155*183	178	382*356*392	160,000	12.0
	13"	7,500	4.0	15,000	335*335*38	330	350*330*360	120,000	11.5

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$
Preheat -Temperature Min(T_{smin}) -Temperature Max(T_{smax}) -Time(min to max)(t_s)	150°C 200°C 60~120sec
T_{smax} to T_L -Ramp-upRate	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6\text{minutes}$

SL32-ASF-Q1 THRU SL34-ASF-Q1**High reliability test capabilities**

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. Operation Life	Ta=25°C,Rated Current (Io=Io max.)Test Duration:1000hrs	MIL-STD-750E METHOD 1027.3
3. High Temperature Reverse Bias	80% Rated VR (Tj=Tj max.)Test Duration:1000hrs	JESD22-A108
4. High Temperature Storage Life	Ta=125°C Test Duration:1000hrs	JESD22 A-103
5. Temperature Cycle	-55°C(15min) to 150°C(15min)Test Cycles:1000cycles	JESD22 A-104
6. Autoclave	P=2atm Ta=121°C RH=100% Test Duration:96hrs	JESD22 A-102
7. Intermittent Operational Life	Ta=25°C,On/Io Max. 2min, Off/2min, Test Cycles:15000cycles	MIL-STD-750E METHOD 1037
8. Solderability	245±5°C for 5sec	J-STD-002
9. Moisture Resistance	Ta=85°C/85% Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
10. Resistance To Solder Heat	260±5°C for 10sec	JESD22 B-106
11. High Temperature High Humidity Reverse Bias	Ta=85°C, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101